

**INDUSTRY STANDARD OF THE
PEOPLE'S REPUBLIC OF CHINA**

SJ 20858-2002

**Measuring methods for electrical parameters of silicon carbide
single crystal material**

碳化硅单晶材料电学参数测试方法
(English Translation)

Issued on: December 12, 2002

Implemented on: May 1, 2003

Issued by: Ministry of Industry and Information Technology of PRC

Table of Contents

What this standard covers	1
Document data	2

What this standard covers

This standard specifies the silicon carbide single crystal material resistivity, Hall mobility testing methods. This standard applies to the temperature at 20°C ~ 700°C range of 4H-SiC, 6H-SiC single crystal materials such as low-resistivity silicon carbide resistivity, Hall mobility measurements.

Document data

Chinese classification (CCS): H82.

Estimated length of the Chinese original: 9,989 words.